

Green Products

SK2S160-100 Power Schottky Rectifier

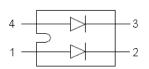
Applications:

- Rectifiers in switch mode power Supplies(SMPS)
- Insulated package(Viso=2500VRMs)
- Free wheeling diode in low voltage Converters

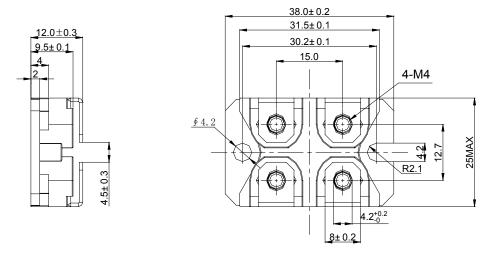
Features:

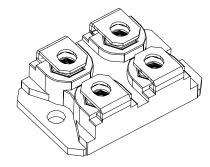
- International standard package SOT-227
- Very low VF
- Extremely low switching losses
- Low IRM-values
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm









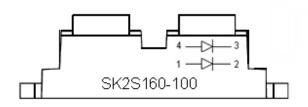
SOT-227

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Marking Diagram:



S = SMC's power module
K = SOT-227 package
2 = Circuit configuration
S = Schottky rectifier
160 = Forward Current (160A)
100 = Reverse Voltage (100V)

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SK2S160-100	SOT-227	10nos / tubo
	(Pb-Free)	10pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	VRRM	-	100		V
Average Forward Current*	I _{F(AV)}	50% duty cycle @T _C = 105°C, rectangular wave form		80 160	Α
Peak One Cycle Non- Repetitive Surge Current (peg leg)	I _{FSM}	8.3 ms, half Sine pulse	1000		Α
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25°C,I _{AS} =12A,L=180μH non repetitive	16		mJ
Total Power Dissipation	P _{tot}	T _C =25℃	150		W
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max.V _A =1.5×V _R typical	1.2		Α

Electrical Characteristics:

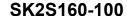
Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@ 80A, Pulse, T _J = 25 °C	0.80	V
	V _{F2}	@ 80A, Pulse, T _J = 125 °C	0.70	V
		@ 160A, Pulse, T _J = 125 °C	0.95	
Reverse Current (per leg) *	L	@V _R = rated V _R	2	mA
	I _{R1}	T _J = 25 °C	2	ША
	I _{R2}	$@V_R = rated V_R$	20	mA
		T _J = 125 °C		
Voltage Rate of Change	dv/dt	-	5000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-40 to +150	°C
Storage Temperature	T _{stg}	-	-40 to +150	°C
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	0.9	°C/W
Maximum Thermal Resistance Junction to Case (per package)	$R_{ heta JC}$	DC operation	0.5	°C/W
Mounting torque(M4)			1.1-1.5/9-13	Nm/
Terminal connection torque(M4)	M_D	-	1.1-1.5/9-13	lb.in.
Typical Approximate Weight	wt	-	30	g
Case Style		SOT-227		

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